Amendments to the Specification:

Please replace the paragraph beginning on page 2, line 1, with the following rewritten paragraph:

Presently, organic luminescent materials used for electroluminescence devices are mainly classified into two groups, namely, a low-molecular group and a high-molecular (or polymer) group. Organic luminescent materials of the low-molecular group are normally subjected to the gaseous phase process such as ~~the~~ vacuum evaporation to form thin films, which are then subjected to patterning using masks. This is disclosed on page 34 of Applied Physics Letters, Vol. 51 (1997), for example. Organic luminescent materials of the polymer group can be dissolved in solvents, so that they are subjected to the application method (or coating method) to form films, which are then subjected to patterning by the liquid-drop discharge method such as the inkjet method. This is disclosed on page 34 of Applied Physics Letters, Vol. 71 (1997), for example. Manufacturing methods for an organic electroluminescence device formed by the liquid-drop discharge method are known, an example of which is disclosed in Japanese Patent Application Publication No. Hei 10-12377.

SB 11-17-06

Please replace the paragraph beginning on page ~~11~~ 10, line ~~1~~ 25, with the following rewritten paragraph:

Numerous display regions R, G, and B (representing ~~read~~red, green and blue colors) having electrodes respectively are arranged in the real display area 4 in such a way that they are independently separated from each other in A-B directions and C-D directions.

SB 11-17-06

Please replace the paragraph beginning on page 14, line ~~16~~ 15, with the following rewritten paragraph:

It is preferable that the pixel electrode 23 ~~have~~has a prescribed thickness ranging from 50 nm to 200 nm, wherein it is preferable to set the thickness to approximately 150 nm. Oxygen (O_2) plasma processing is performed on the surface of the ITO serving as the pixel electrode 23, whereby a lyophilic characteristic is applied to the pixel electrode 23, which is also cleaned on the surface and is adjusted in work function. The O_2 plasma processing is performed under prescribed conditions in which plasma power ranges from 100 kW to 800 kW, oxygen gas flow ranges from 50 ml/min to 100 ml/min, substrate carrying speed ranges from 0.5 mm/sec to 10 mm/sec, and substrate temperature ranges from 70 °C to 90 °C.

SB 11-17-06

Please replace the paragraph beginning on page 19, line 10, with the following rewritten paragraph:

Specifically, as the ligand A; it is preferable to use β-diketone ligands composed of elements such as acetylacetone (acac), dipipaloil methane (dpm), hexafluoro-acetylacetone (hfa), 2,2,6,6-tetramethyl-3,5-octandioacetone (TMOD), thenoyltrifluoroacetone (TTA), 1-phenyl-3-isohepty-1, and 3-propandion (product name: Llx54, Llx51, produced by Henkel Co. Ltd.); it is preferable to use quinolinolic ligands composed of elements such as 8-quinolinole (oxine), and 2-methyl-8-quinolinole; it is preferable to use phosphoric acid ligands composed of elements such as trioctylhoffineoxide (TOPO), tributyl phosphate (TBP), isobutylmethylketone (MBK), and bis (2-ethylhexl) phosphate (D2EHPA); and it is preferable to use carboxylic acid ligands composed of elements such as acetic acid and bezonic acid, and diphenylthiocarbazone ligands, for example. Among them, the complex β-diketone ligands (namely, β-diketone complex) ~~corresponds~~correspond to the acid reagent and multidentate ligands using oxygen atoms; therefore, it can be used to form a stable metallic complex.

SB 1H706

Please replace the paragraph beginning on page 26, line 3, with the following rewritten paragraph:

Subsequently, as shown in FIG. 6D, ion implantation of phosphorus ions is performed using the gate electrodes 242, 252, and 262 as masks on the silicon layers 241, 251, and 261 at a dose rate of about $4\times10^{13}/cm^2$. As a result, lowly concentrated impurities are introduced into the gate electrodes 242, 252, and 262 in a self-alignment manner; therefore, as shown in FIG. 6D, a pair of a low-concentration source region 241b and a low-concentration drain region 241c ~~are~~is formed with respect to the silicon layer 241, and a pair of a low-concentration source region 261b and a low-concentration drain region 261c ~~are~~is formed with respect to the silicon layer 261. In addition, a pair of low-concentration impurity regions 251S and 251D ~~are~~is formed with respect to the silicon layer 251.

SB 1H704

Please replace the paragraph beginning on page 33, line 23, with the following rewritten paragraph:

Thereafter, an enclosing process is performed to form the encapsulating substrate 30, wherein a dryer (or a drying agent) 45 is attached to the interior wall of the encapsulating substrate 30 in order to prevent water or oxygen from penetrating into the organic electroluminescence device; then, the space formed between the substrate 20 and the encapsulating substrate 30 is enclosed by the enclosing resin 40. A thermosetting resin or ~~a~~an ultraviolet-setting resin is used for the enclosing resin 40. Incidentally, the enclosing process is preferably performed in the inert gas atmosphere such as nitrogen, argon, and helium.